Amendment to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (CANCELLED)
2. (CANCELLED)
3. (CANCELLED)
4. (CANCELLED)
5. (CANCELLED)
6. (CANCELLED)
7. (CANCELLED)
8. (CANCELLED)
9. (CURRENTLY AMENDED) A method for forming a dielectric film on a circuit board, comprising the steps of:

(a) reacting an o-aminophenol compound ~~precursor~~ with an aromatic dicarboxylic acid compound ~~precursor~~, both of which ~~precursors~~ compounds are ~~one of mono- and~~ poly-fluorinated, to form a fluorinated o-aminophenol polymer or oligomer;

(b) introducing only thermosetting reactive groups at ends of the fluorinated o-aminophenol polymer or oligomer to form a thermally curable fluorinated o-aminophenol polymer or oligomer precursor;

(c) dissolving the thermally curable fluorinated o-aminophenol polymer or oligomer precursor in an organic solvent to form a varnish;

(d) coating the varnish on a substrate of a circuit board;

(e) heat curing the varnish, whereupon the reactive groups at the ends cross-link, to form the dielectric film on the substrate.

10. (PREVIOUSLY PRESENTED) The method as recited in claim 9, further comprising the step of:

(f) surface polishing the film.

11. (PREVIOUSLY PRESENTED) The method as recited in claim 10, wherein steps (d), (e) and (f) are repeated to form a multilayer circuit board.

12. (PREVIOUSLY PRESENTED) The method as recited in claim 9, wherein step (e) includes heating at 200°C for thirty minutes, and heating at 350°C for 1-2 hours.

13. (PREVIOUSLY PRESENTED) The method as recited in claim 12, wherein prior to said heating step (e), preheating occurs at 100-120°C for about 10-20 minutes.

14. (CURRENTLY AMENDED) The method as recited in claim 9, wherein either or both of the o-aminophenol compound precursor and aromatic dicarboxylic acid compound precursor is chosen to contain at least one benzene ring substituted ~~b~~ by one or more fluorine atoms or trifluoromethyl groups or at least one moiety with one or more trifluoromethyl groups.

15. (PREVIOUSLY PRESENTED) The method as recited in claim 9, wherein the dielectric film is chosen to have a dielectric constant of less than 2.5.

16. (NEW) The method as recited in claim 9, wherein the thermosetting reactive groups are selected from a carboxybenzocyclobutenyl group, a phenylethynyl group, a nadiimide group, a maleimide group and a cyanate ester group.

17. (NEW) The method as recited in claim 9, wherein the o-aminophenol compound and the aromatic dicarboxylic acid compound both contain one or two trifluoromethyl groups.